



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92S Plastic-Encapsulate Transistors

K596 Si N-CHANNEL JUNCTION FET

FEATURES

Power dissipation

P_{CM} : 0.1 W ($T_{amb}=25^{\circ}C$)

Gate Current

I_G : 10 mA

Drain current

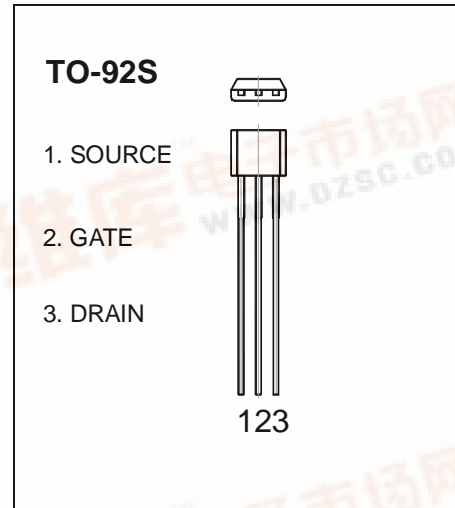
I_D : 1 mA

Drain-Source voltage

BV_{GDO} : -20 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Gate-Drain breakdown Voltage	BV_{GDO}	$I_G = -100\mu A$	-20			V
Gate-Source cut-off Voltage	$V_{GS(off)}$	$V_{DS} = 5V, I_D = 1\mu A$		-0.6	-1.5	V
Drain Current	I_{DSS}	$V_{DS} = 5V, V_{GS} = 0$	100		800	μA
Forward Transfer Admittance	$ Y_{FS} $	$V_{DS} = 5V, V_{GS} = 0, f = 1KHz$	0.4	1.2		mS
Input Capacitance	C_{iss}	$V_{DS} = 5V, V_{GS} = 0, f = 1MHz$		3.5		pF
Output Capacitance	C_{RSS}	$V_{DS} = 5V, V_{GS} = 0$ $f = 1MHz$		0.65		pF

I_{DSS} Classification

Classification	A	B	C	D	E
$I_{DSS} (\mu A)$	100-170	150-240	210-350	320-480	440-800